

Carbon dimer defect as the origin of the 4.1 eV luminescence in hexagonal boron nitride

Mažena Mackoit-Sinkevičienė¹, Marek Maciaszek², Chris G. Van de Walle³,

Audrius Alkauskas¹

¹Center for Physical Sciences and Technology (FTMC), Vilnius LT-10257, Lithuania

²Faculty of Physics, Warsaw University of Technology, Koszykowa 75, 00-662 Warszawa, Poland

³Materials Department, University of California, Santa Barbara, California 93106-5050, USA

mazena.mackoit@ftmc.lt

Hexagonal boron nitride (hBN) has attracted considerable interest over the past decade as a versatile material that can be used in a number of applications due to its unique combination of physical and chemical properties. In as-grown samples bright luminescence with a clear zero-phonon line (ZPL) at 4.1 eV is often observed [1]. The emission is believed to be due to defects. The line can act as a source of single photons [2]. Despite a ubiquitous nature of the 4.1 eV emission, the chemical nature of the defect, which responsible for luminescence, has not been established, even though the involvement of carbon is often assumed [3].

Based on hybrid functional first-principles calculations we propose that the neutral carbon dimer defect, $C_B C_N$, is responsible for the observed emission. We find that neutral $C_B C_N$ is the most stable for Fermi levels throughout most of the band gap, with a formation energy of 2.2 eV. We find that there is a range of atomic chemical potentials and Fermi levels where the dimer is the most stable defect, indicating that it will form whenever carbon is present.

Carbon dimer accounts for all known experimental facts about the 4.1 eV luminescence: the involvement of carbon, the energy of the transition, the very short radiative lifetime, and moderate electron-phonon coupling. All these results allow us to propose the $C_B C_N$ as a defect responsible for the 4.1 eV emission in hBN. In fact, carbon dimer defects have been indeed observed in transmission electron microscopy experiments on hBN [4].

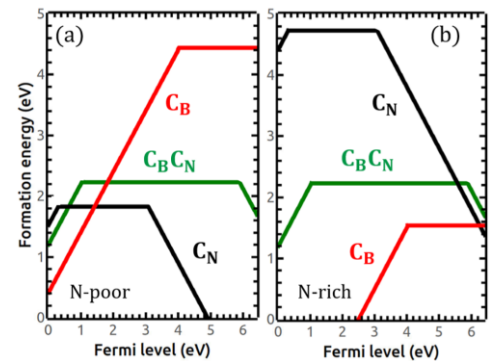


Fig. 1. Formation energy vs. Fermi level for C_B , C_N , and $C_B C_N$ defects in various charge states under (a) N-poor and (b) N-rich conditions.

REFERENCES

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